

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings of claims in the application:

LISTING OF CLAIMS:

1. (Previously Presented) A scale for technical devices which are used for high-resolution or ultrahigh-resolution imaging of structures, the scale comprising:
 - a plurality of one of crystalline and amorphous first material layers having a first thickness; and
 - a plurality of one of crystalline and amorphous second material layers which are distinguishable from the first material layers when imaged using one of high-resolution and ultrahigh-resolution imaging methods, the second material layers having a second thickness and the first material layers alternating with the second material layers,
 - at least one of the first and second material layers having a thickness of less than twenty-five nanometers.
2. (Previously Presented) The scale as recited in claim 1 wherein the first material layers have a different strain than the second material layers.
3. (Previously Presented) The scale as recited in claim 1 wherein both the first and second material layers have a thickness of fewer than ten nanometers.
4. (Previously Presented) The scale as recited in claim 1 wherein the first and second materials layers have different band gaps.
5. (Previously Presented) The scale as recited in claim 1 further comprising a plurality of third material layers having a third thickness different from the second thickness and a plurality of fourth material layers having the same thickness as the first thickness, the third material layers alternating with the fourth material layers.
6. (New) A scale for technical devices which are used for high-resolution or ultrahigh-resolution imaging of structures, the scale comprising:
 - a plurality of one of crystalline and amorphous first material layers having a first thickness; and
 - a plurality of one of crystalline and amorphous second material layers which are distinguishable from the first material layers when imaged using one of high-resolution and ultrahigh-resolution imaging methods, the second material layers having a second thickness and the first material layers alternating with the second material layers, both of the first and second material layers having a thickness of less than ten nanometers,

wherein the first material layers have a different strain than the second material layers, and the first and second materials layers have different band gaps.

7. (New) The scale as recited in claim 6 further comprising a plurality of third material layers having a third thickness different from the second thickness and a plurality of fourth material layers having the same thickness as the first thickness, the third material layers alternating with the fourth material layers.